

PROCESS FOR FABRICATING THIN-FILM DEVICE
AND THIN-FILM DEVICE

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ABSTRACT OF THE DISCLOSURE

In a process for producing a thin-film device, a
10 conducting layer composed of an anodically oxidizable
metal is formed on a substrate and is etched to form gate
bus lines and gate electrode having upper surfaces
parallel to the substrate and inclined side surfaces.
The gate bus lines and the gate electrodes are anodically
15 oxidized, so that they include inner conducting portions
and outer insulating oxide films covering the inner
conducting portions. The outer insulating films prevent
the bus lines from short circuiting, and the inclined
side surfaces of the bus lines makes it possible to
20 fabricate a dense wiring arrangement.